

MOSFET - Power, Single N-Channel, D²PAK7

60 V, 3.7 mΩ, 127 A



ON Semiconductor®

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NTBGS3D5N06C

Features

- Low R_{DS(on)} to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- Lowers Switching Noise/EMI
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Power Tools, Battery Operated Vacuums
- UAV/Drones, Material Handling
- BMS/Storage, Home Automation

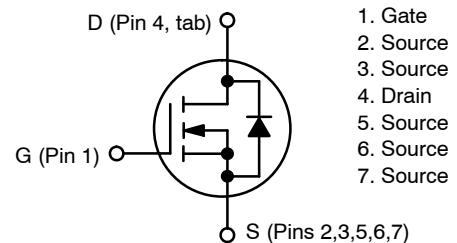
MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V _{DSS}	60	V	
Gate-to-Source Voltage	V _{GS}	±20	V	
Continuous Drain Current R _{θJC} (Note 2)	I _D	127	A	
Power Dissipation R _{θJC} (Note 2)				P _D
Continuous Drain Current R _{θJA} (Notes 1, 2)	I _D	22	A	
Power Dissipation R _{θJA} (Notes 1, 2)				P _D
Pulsed Drain Current	T _A = 25°C, t _p = 100 μs	I _{DM}	491	A
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C	
Source Current (Body Diode)	I _S	95	A	
Single Pulse Drain-to-Source Avalanche Energy (I _L = 18.8 A _{pk} , L = 1 mH)	E _{AS}	176	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T _L	260	°C	

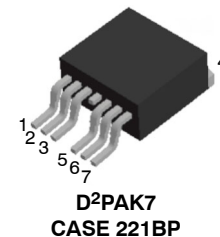
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using a 1 in², 1 oz. Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

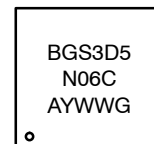
V _{(BR)DSS}	R _{DS(ON) MAX}	I _{D MAX}
60 V	3.7 mΩ @ 12 V	127 A
	4.1 mΩ @ 10 V	



N-CHANNEL MOSFET



MARKING DIAGRAM



BGS3D5N06C= Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NTBGS3D5N06C	D ² PAK7 (Pb-Free)	800 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	1.3	°C/W
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 250\ \mu\text{A}$, ref to 25°C		19.2		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 60\text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 122\ \mu\text{A}$	2.0		4.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	$I_D = 122\ \mu\text{A}$, ref to 25°C		-8		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 12\text{ V}, I_D = 24\text{ A}$		3.1	3.7	m Ω
		$V_{GS} = 10\text{ V}, I_D = 12\text{ A}$		3.25	4.1	
Gate-Resistance	R_G	$T_A = 25^\circ\text{C}$		1.2		Ω

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}, f = 1\text{ MHz}$		2430		pF
Output Capacitance	C_{OSS}			1290		
Reverse Transfer Capacitance	C_{RSS}			21		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 10\text{ V}, V_{DS} = 30\text{ V}; I_D = 24\text{ A}$		39		nC
Threshold Gate Charge	$Q_{G(TH)}$			6.4		
Gate-to-Source Charge	Q_{GS}			9.5		
Gate-to-Drain Charge	Q_{GD}			4.5		
Output Charge	Q_{OSS}	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}$		69		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 30\text{ V}, I_D = 24\text{ A}, R_G = 6\ \Omega$		14.4		ns
Rise Time	t_r			6.9		
Turn-Off Delay Time	$t_{d(OFF)}$			28.9		
Fall Time	t_f			9.7		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 24\text{ A}$	$T_J = 25^\circ\text{C}$		0.81	1.2	V
			$T_J = 125^\circ\text{C}$		0.68		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, di_S/dt = 100\text{ A}/\mu\text{s}, I_S = 12\text{ A}$			55		ns
Reverse Recovery Charge	Q_{RR}				52		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

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TYPICAL CHARACTERISTICS

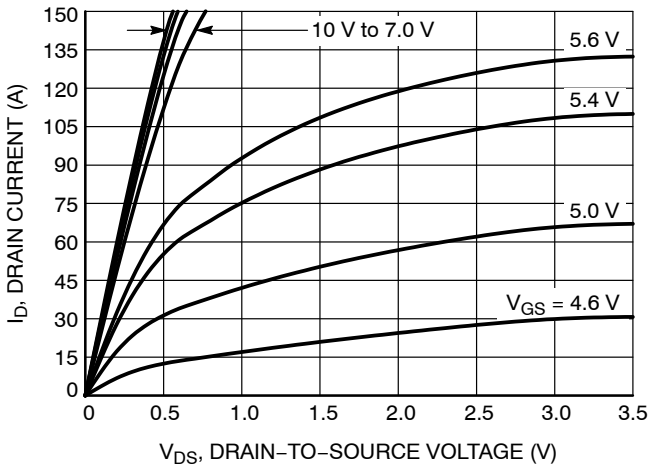


Figure 1. On-Region Characteristics

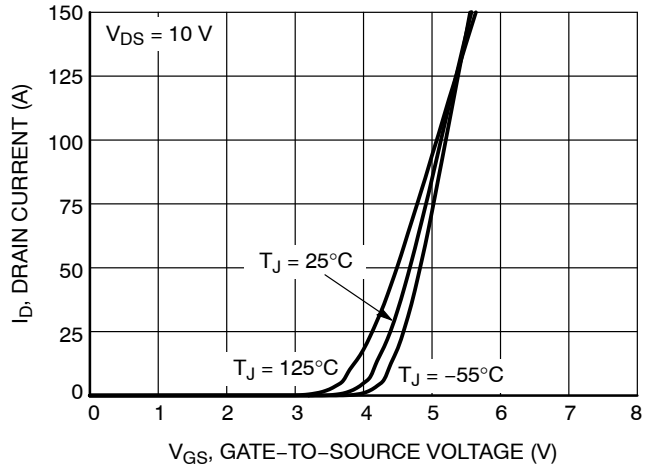


Figure 2. Transfer Characteristics

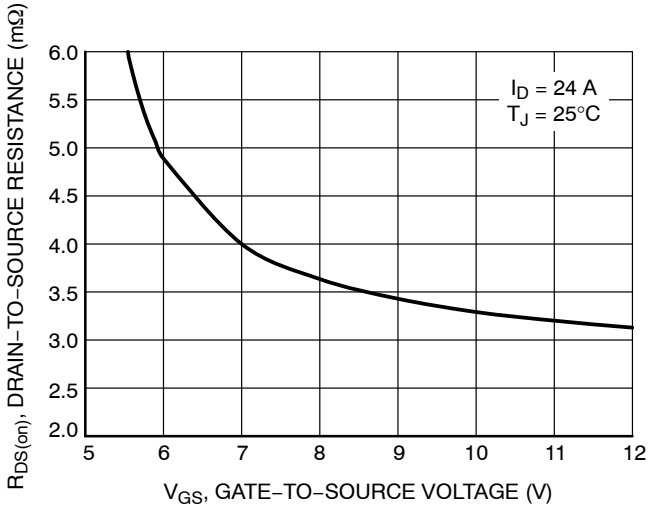


Figure 3. On-Resistance vs. Gate-to-Source Voltage

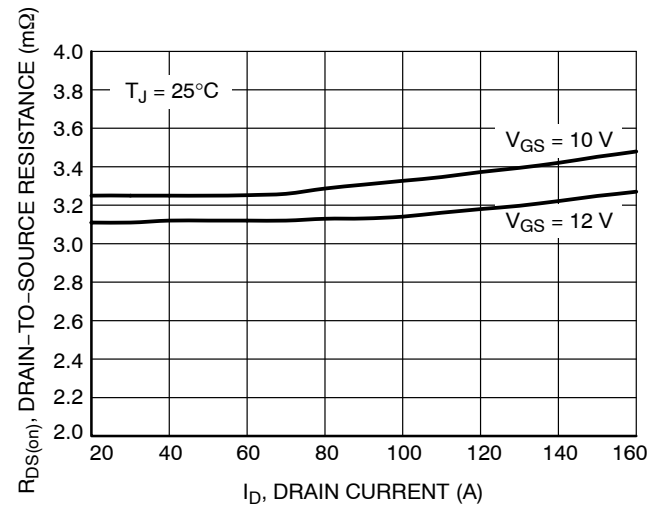


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

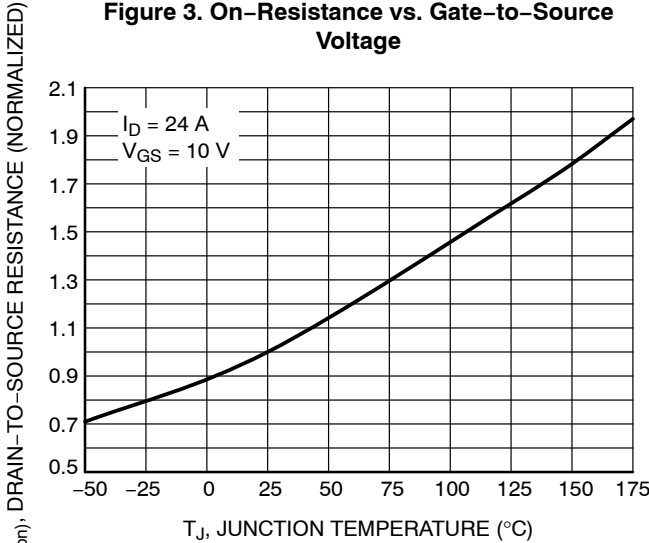


Figure 5. On-Resistance Variation with Temperature

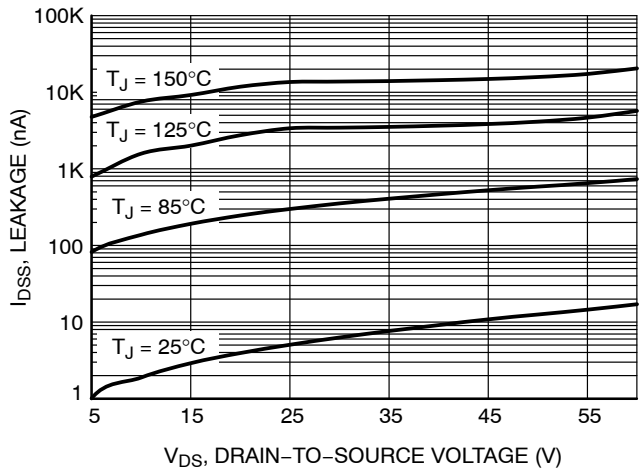


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

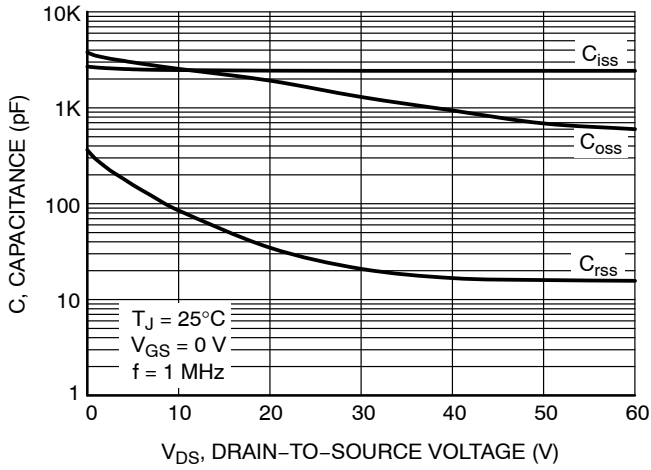


Figure 7. Capacitance Variation

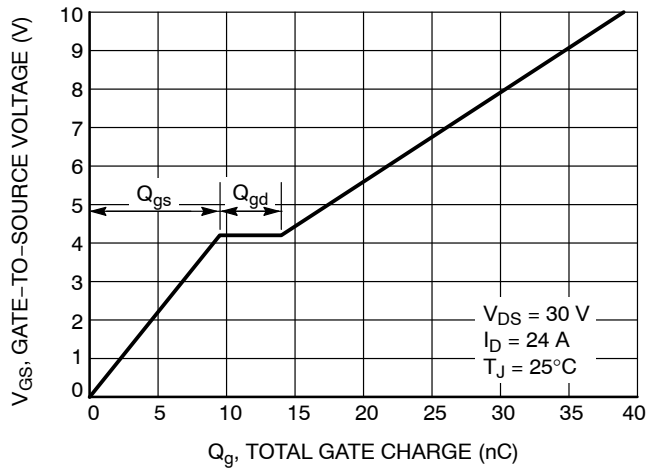


Figure 8. Gate-to-Source vs. Total Charge

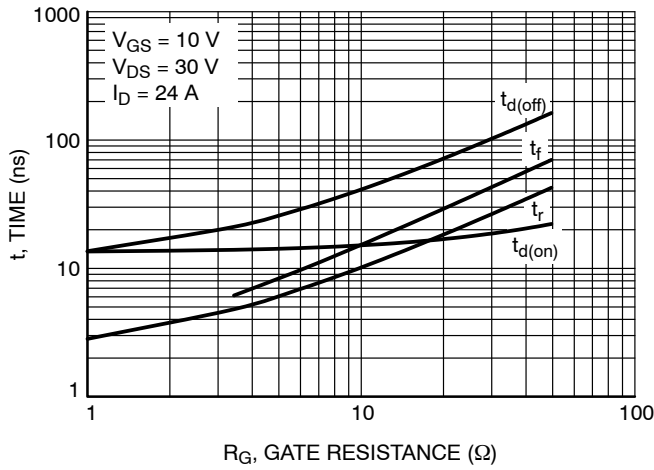


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

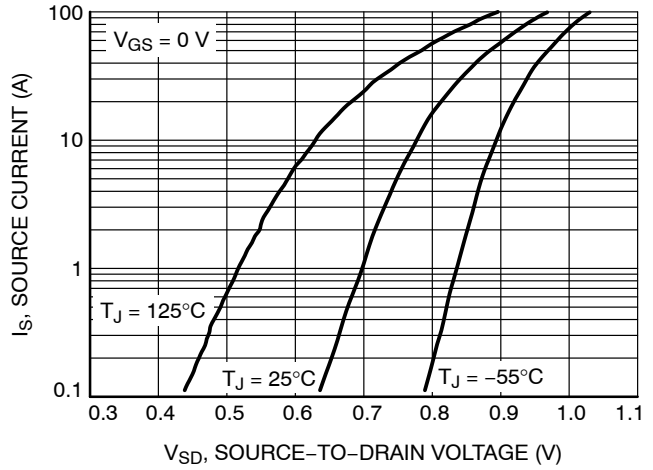


Figure 10. Diode Forward Voltage vs. Current

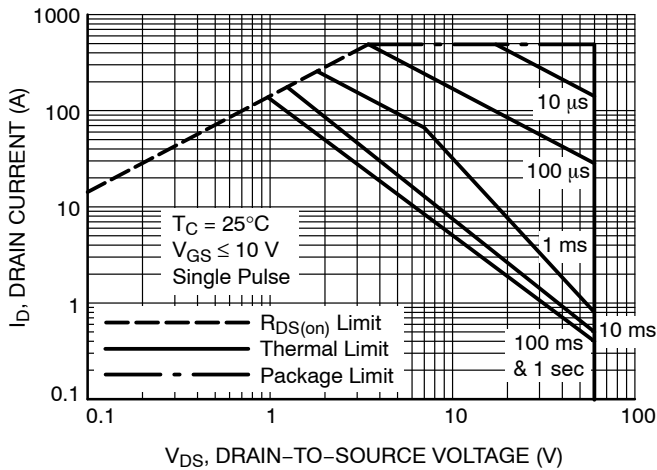


Figure 11. Maximum Rated Forward Biased Safe Operating Area

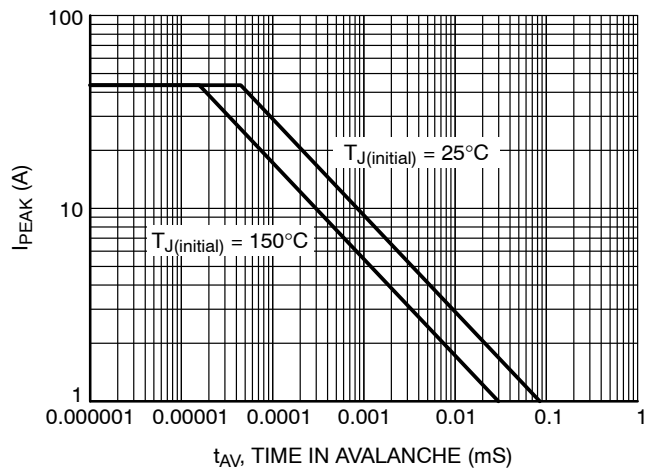


Figure 12. Maximum Drain Current vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

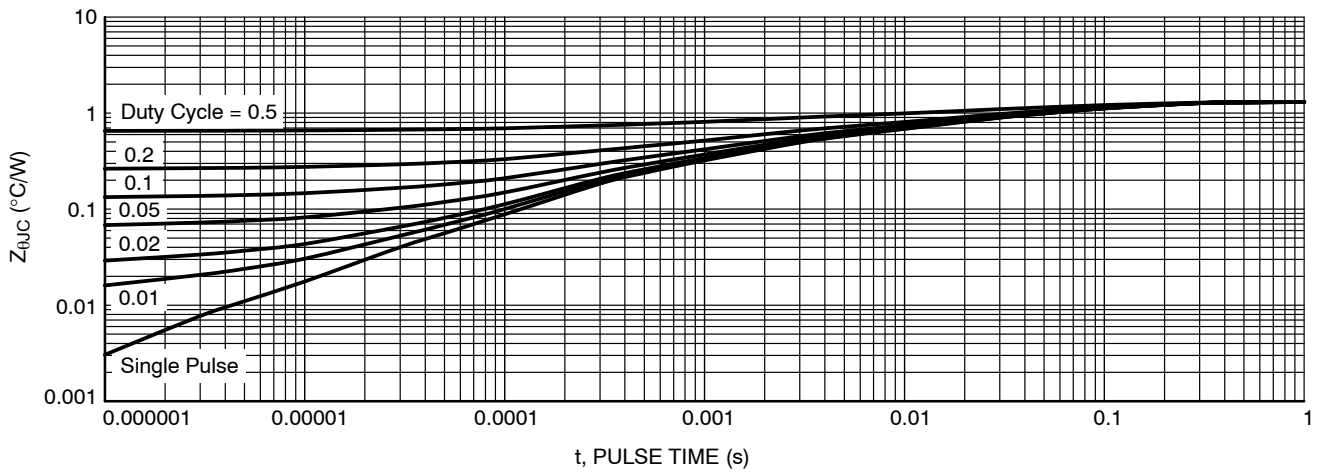
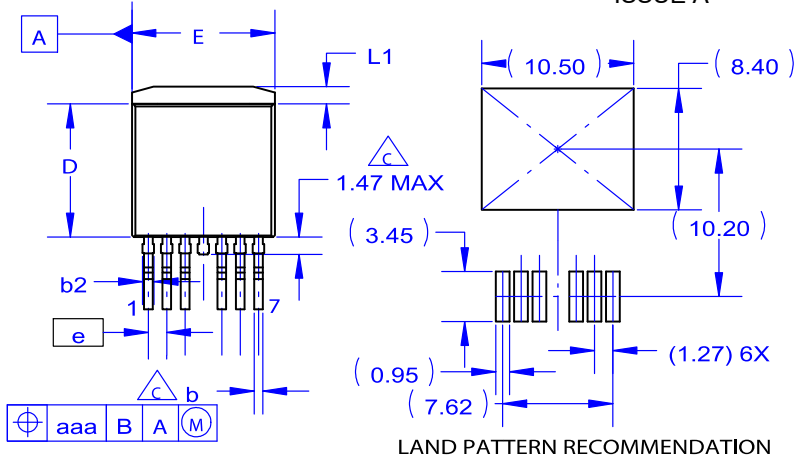


Figure 13. Transient Thermal Impedance

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PACKAGE DIMENSIONS

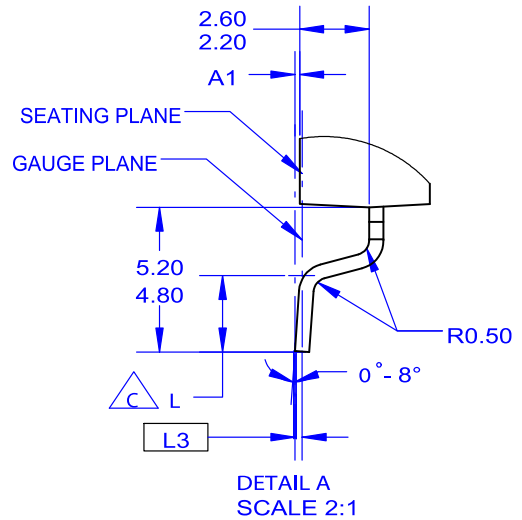
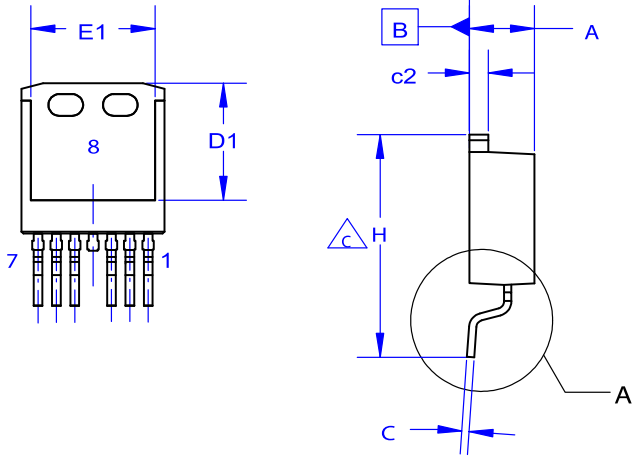
D2PAK7 (TO-263-7LD) 15.4x9.9x4.5
 CASE 221BP
 ISSUE A



NOTES:

- A. PACKAGE CONFORMS TO JEDEC TO-263 VARIATION CB EXCEPT WHERE NOTED.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- △ OUT OF JEDEC STANDARD VALUE.
- D. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- E. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- F. LAND PATTERN RECOMMENDATION PER IPC. TO127P1524X465-8N.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	0.00	0.10	0.20
b2	0.60	0.70	0.80
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.20	1.30	1.40
D	9.00	9.20	9.40
D1	7.30	7.80	8.20
E	9.70	9.90	10.20
E1	7.15	8.05	8.55
e	~	1.27	~
H	15.10	15.40	15.70
L	2.44	2.64	2.84
L1	1.00	1.20	1.40
L3	~	0.25	~
aaa	~	~	0.25



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